

PHT4NQ10T

TrenchMOS™ standard level FET

Rev. 02 — 2 May 2002

Product data

1. Description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™ technology.

Product availability:

PHT4NQ10T in SOT223.

2. Features

- TrenchMOS™ technology
- Very fast switching
- Surface mount package.

3. Applications

- Primary side switch in DC to DC converters
- High speed line driver
- Fast general purpose switch.

4. Pinning information

Table 1: Pinning - SOT223, simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1	gate (g)	SOT223	
2	drain (d)		
3	source (g)		
4	drain (d)		

5. Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Typ	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_J \leq 150\text{ °C}$	-	100	V
I_D	drain current (DC)	$T_{sp} = 25\text{ °C}; V_{GS} = 10\text{ V}$	-	3.5	A
P_{tot}	total power dissipation	$T_{sp} = 25\text{ °C}$	-	6.9	W
T_J	junction temperature		-	150	°C
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 1.75\text{ A}$			
		$T_J = 25\text{ °C}$	200	250	mΩ
		$T_J = 150\text{ °C}$	-	575	mΩ

6. Limiting values

Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

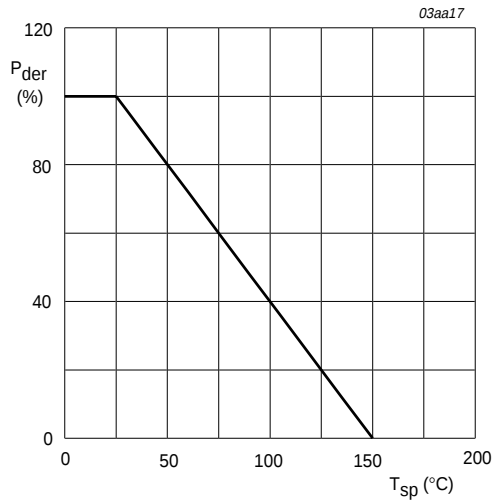
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_J \leq 150\text{ °C}$	-	100	V
V_{DGR}	drain-gate voltage (DC)	$25\text{ °C} \leq T_J \leq 150\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage (DC)		-	±20	V
I_D	drain current (DC)	$T_{sp} = 25\text{ °C}; V_{GS} = 10\text{ V};$ Figure 2 and 3	-	3.5	A
		$T_{sp} = 100\text{ °C}; V_{GS} = 10\text{ V};$ Figure 2	-	2.2	A
I_{DM}	peak drain current	$T_{sp} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s};$ Figure 3	-	14	A
P_{tot}	total power dissipation	$T_{sp} = 25\text{ °C};$ Figure 1	-	6.9	W
T_{stg}	storage temperature		-65	+150	°C
T_J	junction temperature		-65	+150	°C

Source-drain diode

I_S	source (diode forward) current (DC)	$T_{sp} = 25\text{ °C}$	-	3.5	A
I_{SM}	peak source (diode forward) current	$T_{sp} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	14	A

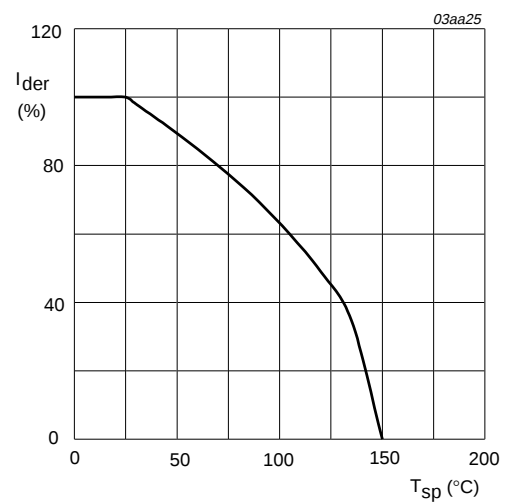
Avalanche ruggedness

$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; $I_D = 3.5\text{ A};$ $t_p = 0.2\text{ ms}; V_{DD} \leq 15\text{ V}; R_{GS} = 50\text{ }\Omega;$	-	45	mJ
$I_{DS(AL)SM}$	peak non-repetitive drain-source avalanche current	$V_{GS} = 10\text{ V};$ starting $T_J = 25\text{ °C};$ Figure 4	-	3.5	A



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

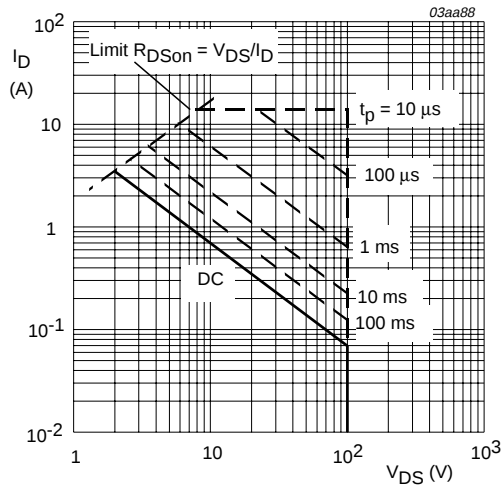
Fig 1. Normalized total power dissipation as a function of solder point temperature.



$$V_{GS} \geq 10 \text{ V}$$

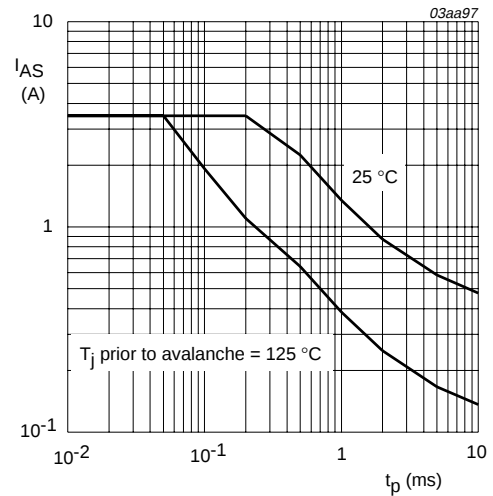
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of solder point temperature.



$T_{sp} = 25^{\circ}C$; I_{DM} is single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.



Unclamped inductive load; $V_{DD} \leq 15 \text{ V}$; $R_{GS} = 50 \Omega$; $V_{GS} = 10 \text{ V}$; starting $T_j = 25^{\circ}C$ and $125^{\circ}C$.

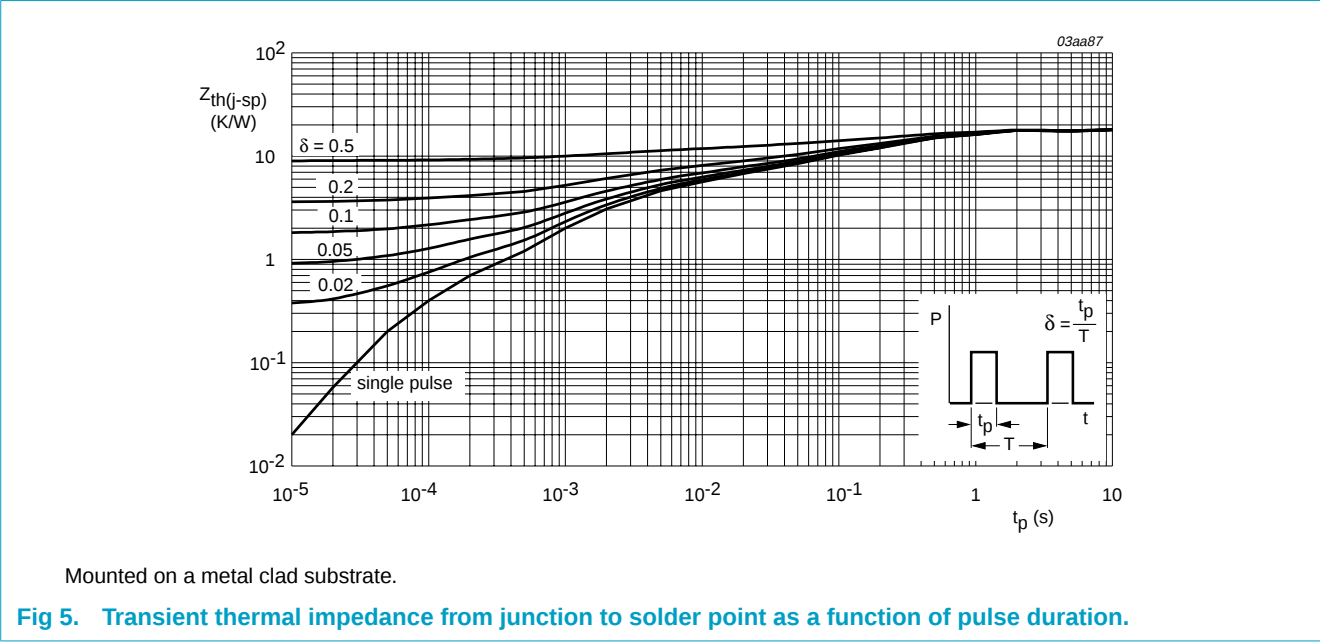
Fig 4. Non-repetitive avalanche ruggedness current as a function of pulse duration.

7. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	mounted on a metal clad substrate; Figure 5	-	-	18	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed circuit board; minimum footprint	-	150	-	K/W

7.1 Transient thermal impedance

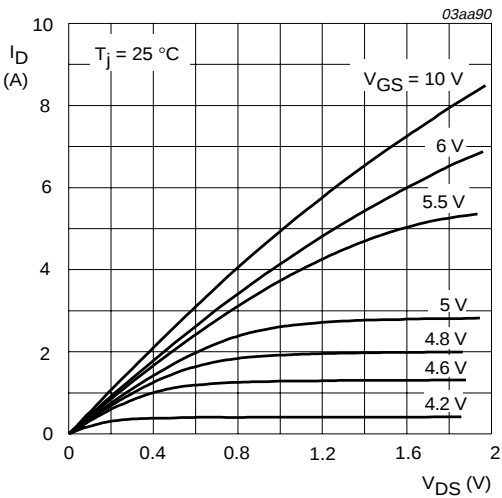


8. Characteristics

Table 5: Characteristics

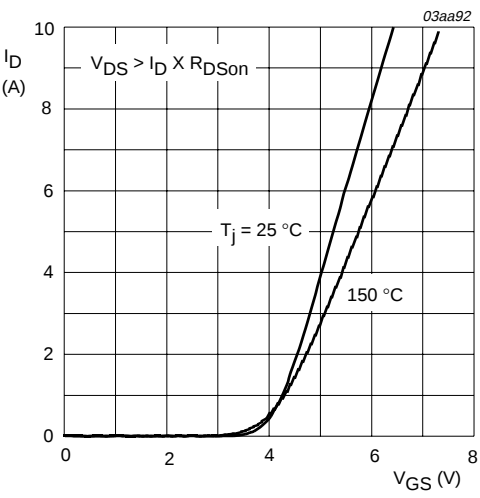
$T_j = 25\text{ °C}$ unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V				
		T _J = 25 °C	100	130	-	V
		T _J = −55 °C	89	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS}				
		T _J = 25 °C; Figure 10	2	3	4	V
		T _J = 150 °C; Figure 10	1.2	-	-	V
		T _J = −55 °C; Figure 10	-	-	6	V
I _{DSS}	drain-source leakage current	V _{DS} = 100 V; V _{GS} = 0 V				
		T _J = 25 °C	-	1	25	μA
		T _J = 150 °C	-	4	250	μA
		V _{DS} = 60 V; V _{GS} = 0 V				
		T _J = 85 °C	-	-	1	μA
I _{GSS}	gate-source leakage current	V _{GS} = ±20 V; V _{DS} = 0 V	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 1.75 A				
		T _J = 25 °C; Figure 8 and 9	-	200	250	mΩ
		T _J = 150 °C; Figure 9	-	-	575	mΩ
Dynamic characteristics						
g _{fs}	forward transconductance	V _{DS} = 5 V; I _D = 3.5 A; Figure 12	-	4.2		S
Q _{g(tot)}	total gate charge	I _D = 3.5 A; V _{DS} = 80 V;	-	7.4	-	nC
Q _{gs}	gate-source charge	V _{GS} = 10 V; Figure 15	-	1.5	-	nC
Q _{gd}	gate-drain (Miller) charge		-	3.3	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V;	-	300	-	pF
C _{oss}	output capacitance	f = 1 MHz; Figure 13	-	44	-	pF
C _{rss}	reverse transfer capacitance		-	21	-	pF
t _{d(on)}	turn-on delay time	V _{DD} = 50 V; R _D = 15 Ω;	-	8	-	ns
t _r	rise time	V _{GS} = 10 V; R _G = 6 Ω	-	13	-	ns
t _{d(off)}	turn-off delay time		-	20	-	ns
t _f	fall time		-	11	-	ns
Source-drain diode						
V _{SD}	source-drain (diode forward) voltage	I _S = 3.5 A; V _{GS} = 0 V; Figure 14	-	0.87	1.5	V
t _{rr}	reverse recovery time	I _S = 3.5 A;	-	50	-	ns
Q _r	recovered charge	dI _S /dt = −100 A/μs; V _{GS} = 0 V; V _{DS} = 30 V	-	100	-	nC



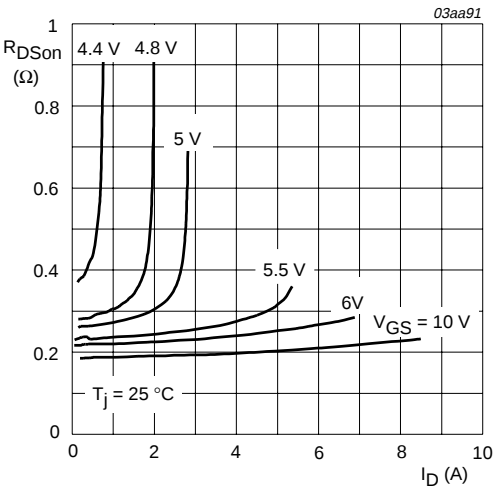
$T_j = 25\text{ °C}$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values.



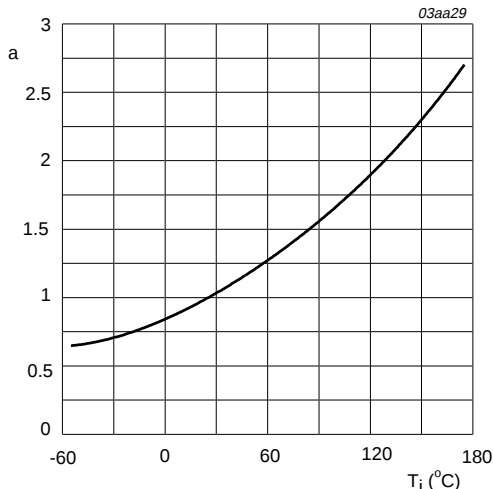
$T_j = 25\text{ °C}$ and 150 °C ; $V_{DS} > I_D \times R_{DSon}$

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



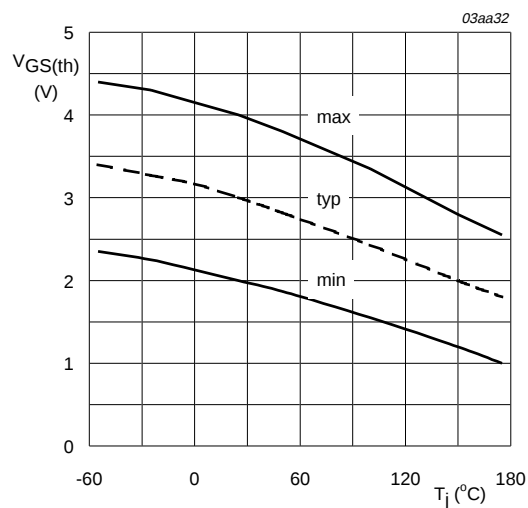
$T_j = 25\text{ °C}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values.



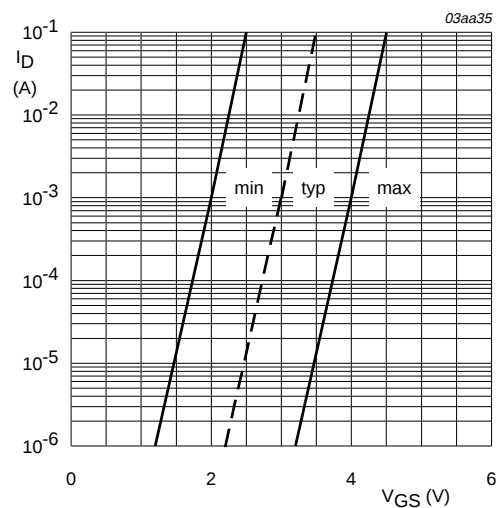
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

Fig 9. Normalized drain-source on-state resistance factor as a function of junction temperature.



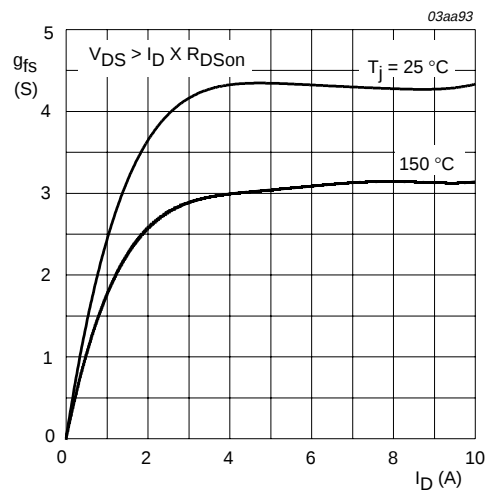
$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature.



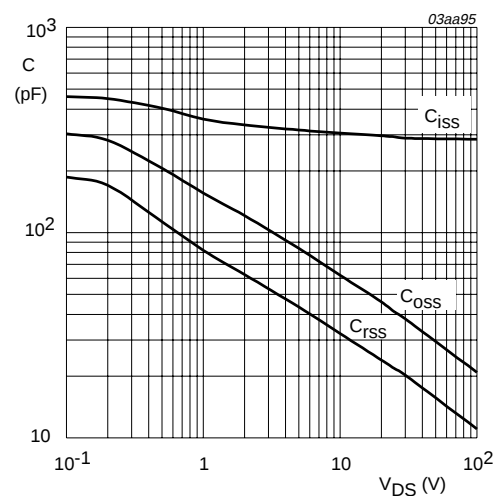
$T_j = 25 \text{ °C}$; $V_{DS} = 5 \text{ V}$

Fig 11. Sub-threshold drain current as a function of gate-source voltage.



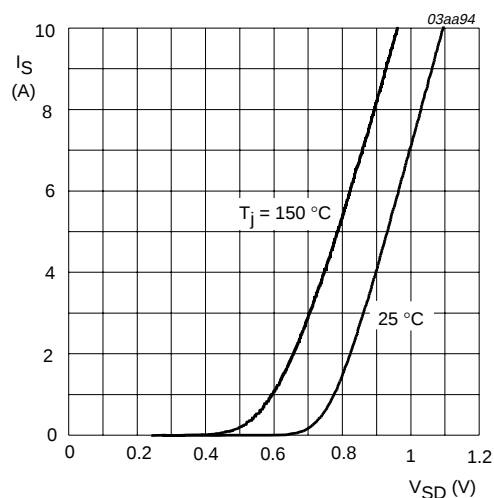
$T_j = 25 \text{ °C}$ and 150 °C ; $V_{DS} > I_D \times R_{DSon}$

Fig 12. Forward transconductance as a function of drain current; typical values.



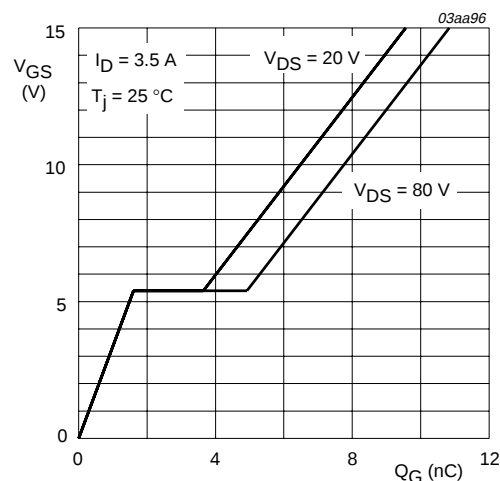
$V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$T_j = 25\text{ °C}$ and 150 °C ; $V_{GS} = 0\text{ V}$

Fig 14. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



$I_D = 3.5\text{ A}$; $V_{DS} = 80\text{ V}$

Fig 15. Gate-source voltage as a function of gate charge; typical values.

9. Package outline

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223

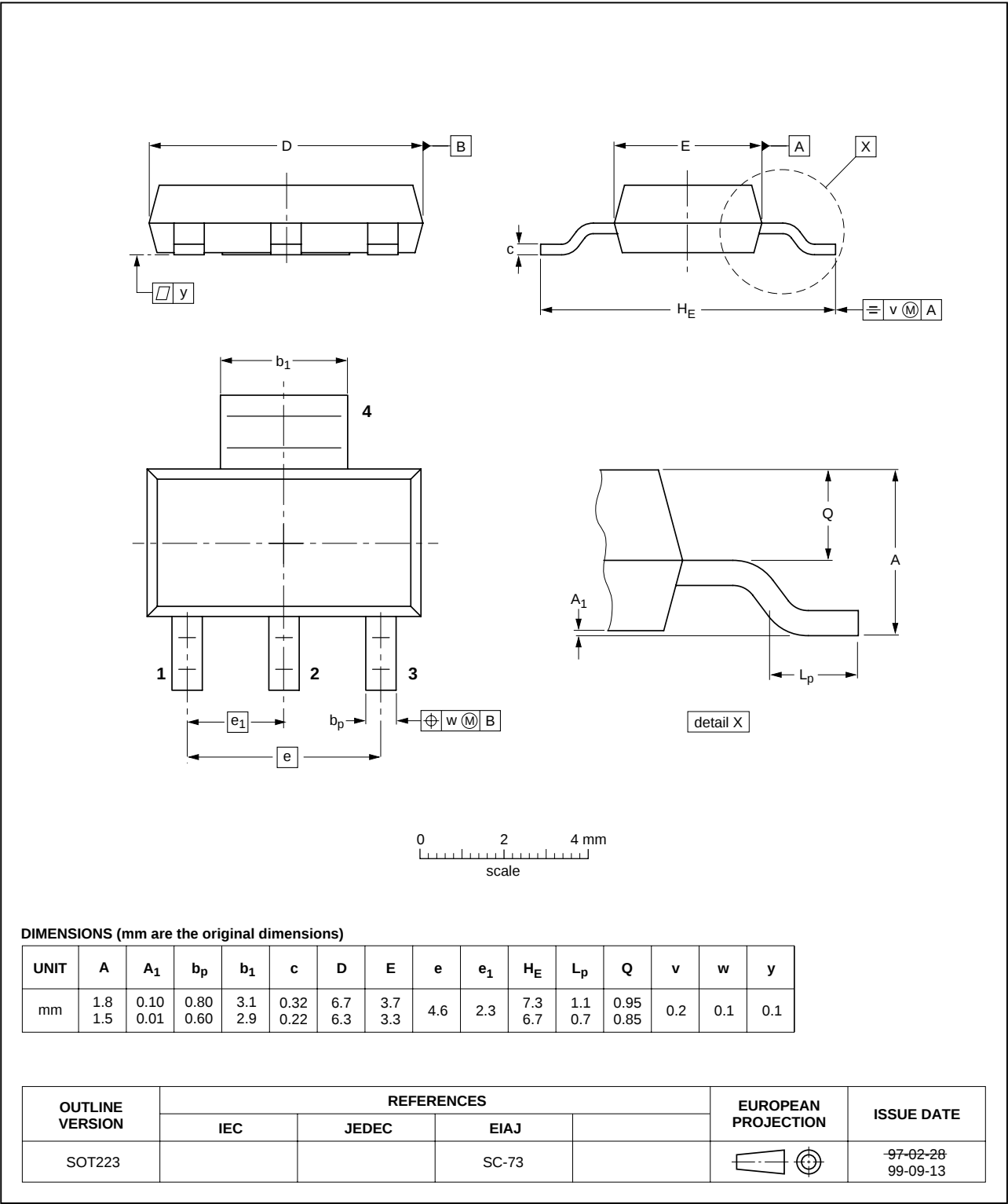


Fig 16. SOT223.

10. Revision history

Table 6: Revision history

Rev	Date	CPCN	Description
02	20020502	-	Product data (9397 750 09581) Modifications: • Additional I_{DSS} data added.
01	20000731	-	Product specification; initial version.

11. Data sheet status

Data sheet status ^[1]	Product status ^[2]	Definition
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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